**Product data sheet** 

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Trench MOSFET technology
- Very fast switching
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

## 3. Applications

- · Charging switch for portable devices
- DC-to-DC converters
- · Power management in battery-driven portables
- · Hard disk and computing power management

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	٧
$V_{GS}$	gate-source voltage			-20	-	20	٧
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	13	Α
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A}; T_j = 25 \text{ °C}$		-	12	14.5	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 1 1 1 6	D I
2	D	drain		
3	G	gate	2 5	
4	S	source	3 8 4	Š
5	D	drain	Transparent top view	017aaa253
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
PMPB11EN	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
PMPB11EN	1C

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## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	13	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	9	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	5.7	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	34	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	n diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	2.2	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

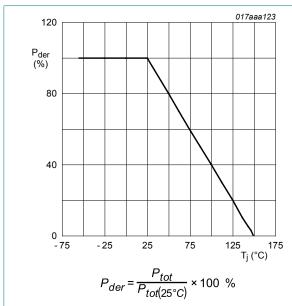


Fig. 1. Normalized total power dissipation as a function of junction temperature

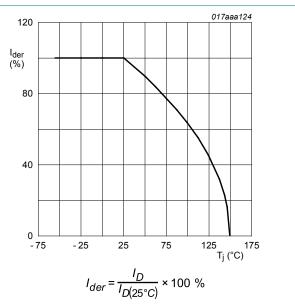
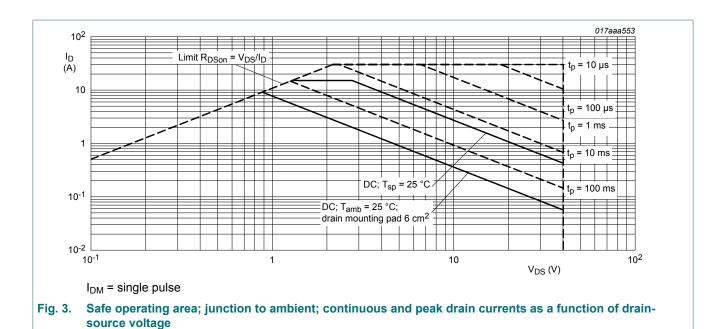


Fig. 2. Normalized continuous drain current as a function of junction temperature

#### 30 V, N-channel Trench MOSFET



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance	in free air	[1]	-	235	270	K/W
	_		[2]	-	67	74	K/W
			[3]	-	33	36	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>,  $t \le 5$  s

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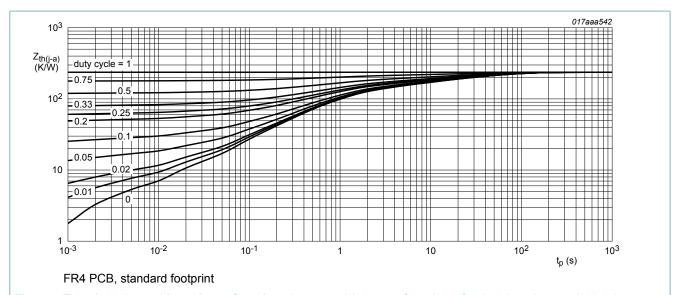


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

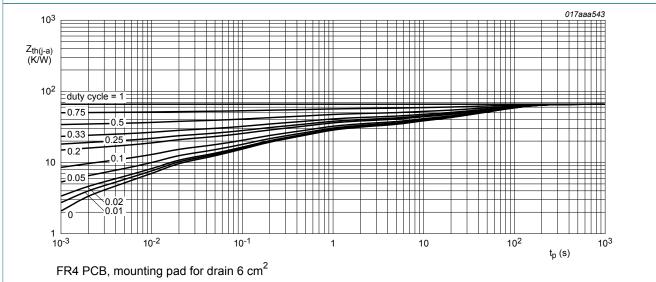


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	ecteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	1	1.5	2	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	20	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 25 °C	-	12	14.5	mΩ
resistance	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 150 °C	-	18	20.5	mΩ
	$V_{GS}$ = 4.5 V; $I_D$ = 3.7 A; $T_j$ = 25 °C	-	14	16.5	mΩ	
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 9 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	45	-	S
$R_G$	gate resistance	f = 1 MHz	-	1.6	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 15 \text{ V}; I_D = 6 \text{ A}; V_{GS} = 10 \text{ V};$	-	13.7	20.6	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	1.73	-	nC
$Q_{GD}$	gate-drain charge		-	1.71	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	840	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	155	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	65	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 15 \text{ V}; I_D = 5 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	9	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	10	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	17	-	ns
t <sub>f</sub>	fall time		-	9	-	ns
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 2.2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.8	1.2	V
	-					

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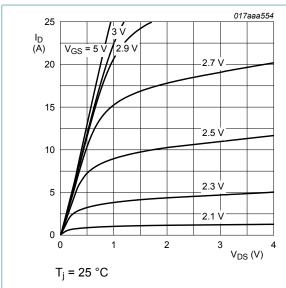


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

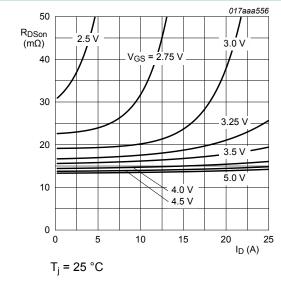


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

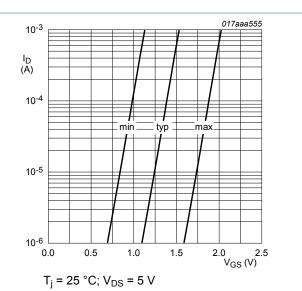


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

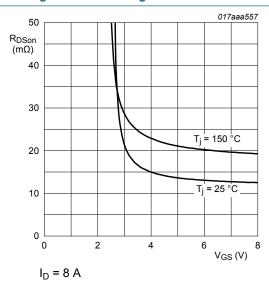


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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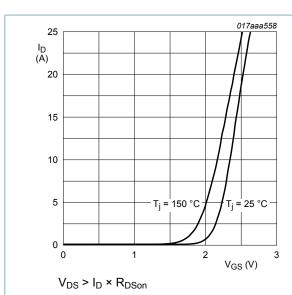


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

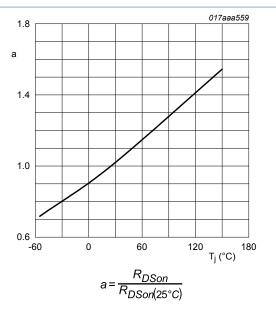


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

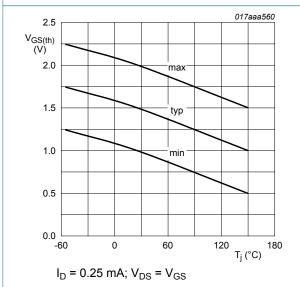


Fig. 12. Gate-source threshold voltage as a function of junction temperature

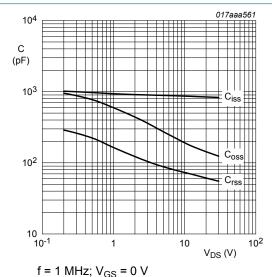


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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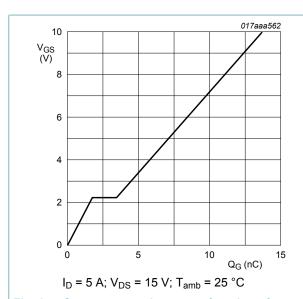


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

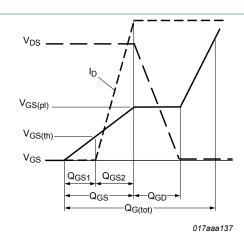


Fig. 15. Gate charge waveform definitions

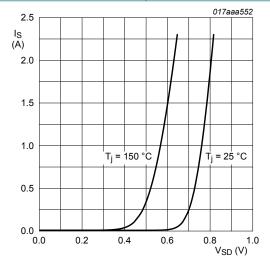
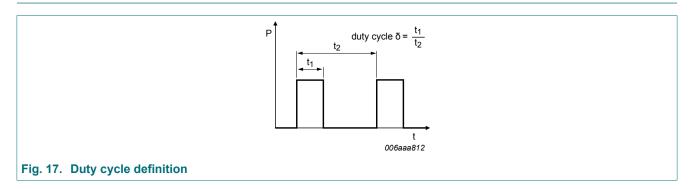


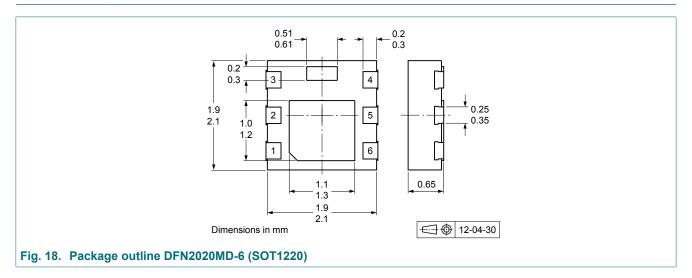
Fig. 16. Source current as a function of source-drain voltage; typical values

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## 11. Test information

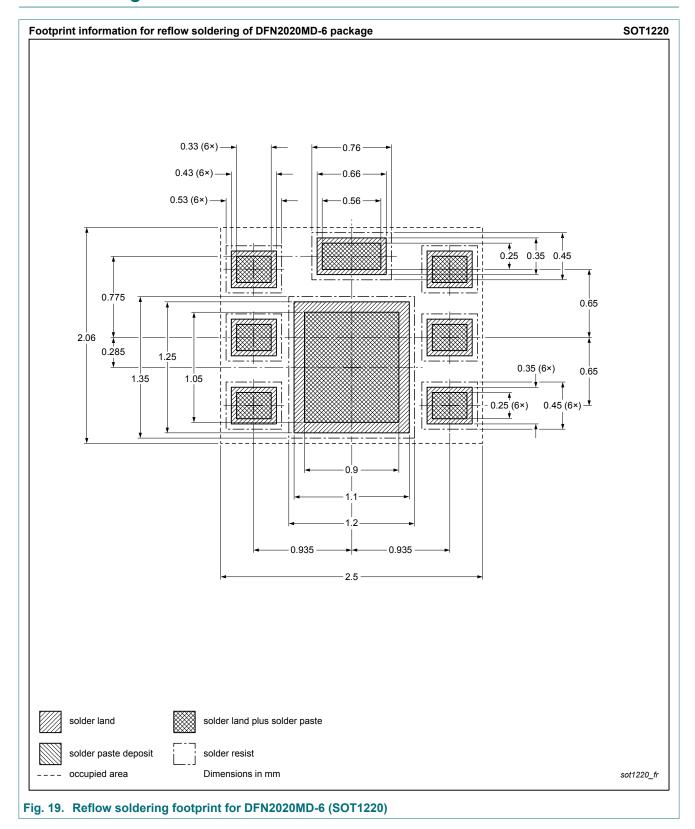


# 12. Package outline



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## 13. Soldering



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# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMPB11EN v.3	20180712	Product data sheet	-	PMPB11EN v.2			
Modifications:	<ul> <li>Adaption of maximum value of I<sub>GSS</sub> to minus</li> <li>Adaption of the typical value of g<sub>fs</sub> according to new wafer fab</li> </ul>						
PMPB11EN v.2	20140114	Product data sheet	-	PMPB11EN v.1			
PMPB11EN v.1	20120516	Product data sheet	-	-			

#### 30 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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